

Anisotropic Swelling and Fracture of Silicon Nanowires during Lithiation

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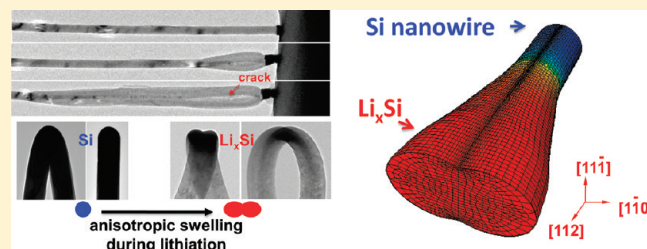
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S Supporting Information

ABSTRACT: We report direct observation of an unexpected anisotropic swelling of Si nanowires during lithiation against either a solid electrolyte with a lithium counter-electrode or a liquid electrolyte with a LiCoO₂ counter-electrode. Such anisotropic expansion is attributed to the interfacial processes of accommodating large volumetric strains at the lithiation reaction front that depend sensitively on the crystallographic orientation. This anisotropic swelling results in lithiated Si nanowires with a remarkable dumbbell-shaped cross section, which develops due to plastic flow and an ensuing necking instability that is induced by the tensile hoop stress buildup in the lithiated shell. The plasticity-driven morphological instabilities often lead to fracture in lithiated nanowires, now captured in video. These results provide important insight into the battery degradation mechanisms.

KEYWORDS: Silicon nanowire, lithium ion battery, anisotropic swelling, volume expansion, fracture, in situ TEM



Lithium ion batteries (LIBs) hold great promise for demanding applications such as electric vehicles.^{1,2} Silicon is being considered as a candidate anode material in LIBs, as it possesses the highest specific capacity among all materials ($\sim 3579 \text{ mAh g}^{-1}$ for Li₁₅Si₄),^{3–6} over an order of magnitude higher than that of carbonaceous anodes used in current LIBs. However, during electrochemical lithiation, Si electrodes experience large volume expansion up to $\sim 300\%$, leading to pulverization and huge capacity loss even in the first cycle.^{1,7–25} While Si has been intensively studied in real and bulk electrochemical cells,^{4,5,7–12,15,19,26–32} and impressive colossal volume change was directly observed with in situ optical microscopy and atomic force microscopy,^{7,26}

it still remains unclear how cracks initiate and evolve at the atomic scale. Although decrease of Si to nanoscale can alleviate pulverization, and nano-Si has been recognized as a promising anode for Li-ion batteries, the poor cyclability still remains and the mechanism behind is not fully understood.^{9,10} A fundamental understanding of the deformation and fracture mechanisms in lithiated Si may help develop strategies to accommodate or mitigate the large expansion and crack formation during cycling, thus paving the way for the application of Si as a high energy

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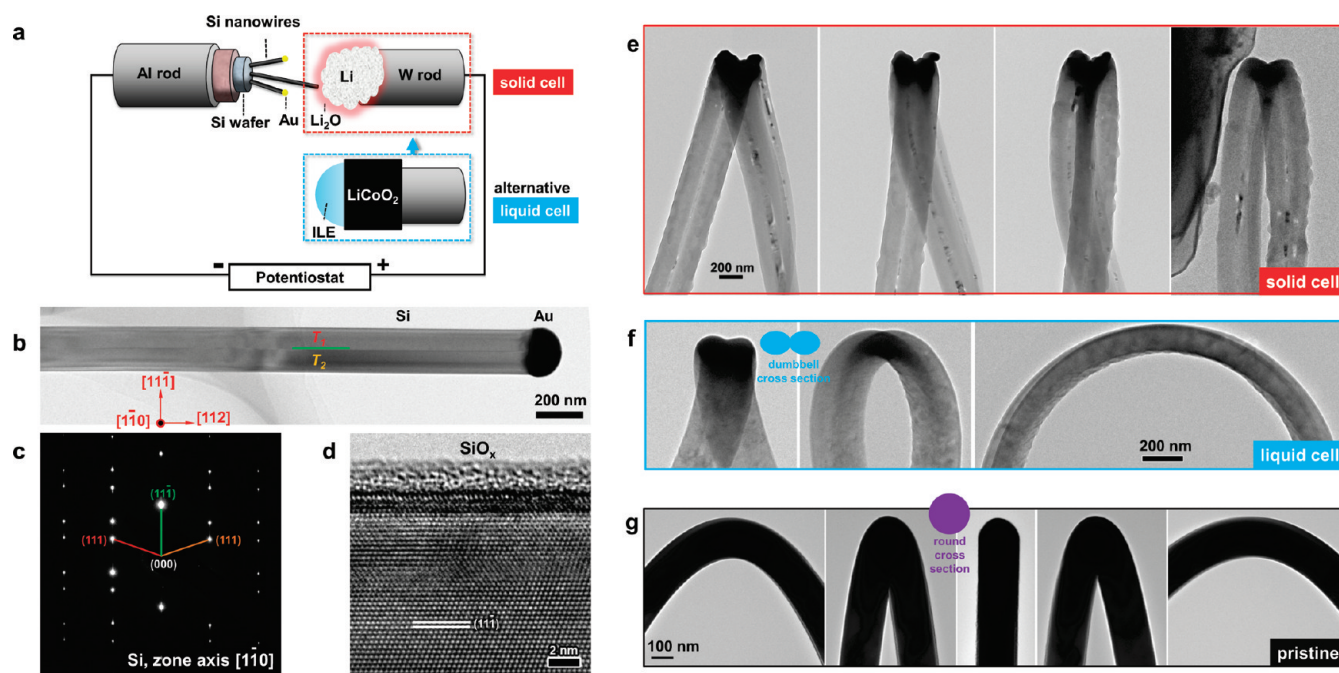


Figure 1. Anisotropic swelling of Si nanowires during lithiation. (a) Schematic illustration of the in situ experimental setup for an all-solid electrochemical cell using Li metal counter electrode (“solid cell”) and a “liquid cell” using the ionic liquid electrolyte and LiCoO₂ counter-electrode for Si lithiation tests. (b–d) Microstructure of a typical pristine Si nanowire. The nanowire had uniform diameter and a twin boundary in the center (b), consistent with the electron diffraction pattern (EDP) in (c). There was a 2 nm thick native amorphous oxide layer on the surface (d). (e–g) Tilted series images showing the same dumbbell shape of the lithiated Si nanowires in a solid cell (e) or in a liquid cell (f), in contrast to the round cross section of the pristine Si nanowire (g).

density electrode in LIBs.^{33–35} In this development, from both practical and fundamental standpoints, what happens to crystalline silicon in the first cycle of lithiation is critically important.

We report here anisotropic swelling of Si nanowires during lithiation in either a conventional liquid cell or an all-solid electrochemical cell inside a transmission electron microscope (TEM), with the latter consisting of a single Si nanowire working-electrode, a nonconventional Li₂O solid electrolyte, and a bulk Li metal counter-electrode. Figure 1a shows the schematic illustration of our experimental setup. Fresh Li metal was loaded as the Li source and reference electrode in the solid cell. Compared to our previous experimental setup (i.e., the liquid cell) where an ionic liquid electrolyte (ILE) was used,^{3,33,36–38} the solid cell configuration offers the advantage of one-dimensional Li transport along the Si nanowire and directly observing the microstructure evolution from the very beginning of the lithiation process. A naturally grown Li₂O layer (~700 nm thick) was formed on the surface of the Li metal by air exposure (~2 s) and used as solid electrolyte between the Si working and Li counter-electrodes (Figure S1, Supporting Information). Si nanowires that were grown by vapor–liquid–solid growth (VLS) from Au catalyst islands on a Si wafer were affixed to a scanning tunneling microscopic (STM) probe and then translated via piezopositioners to approach the Li₂O electrolyte using Li counter-electrode. Panels b–d of Figures 1 show the typical microstructure of the pristine Si nanowires used in this study. The Si nanowires were grown along the $[11\bar{2}]$ direction, usually with a 180° twin boundary parallel to the $(11\bar{1})$ plane (Figure 1b, c) and a 2 nm thick native oxide layer on the surface (Figure 1d). Because the Li₂O layer formed a large barrier for Li⁺ transport,³⁹ a potential of –2 V applied to the Si nanowire versus the Li

counter electrode was necessary to promote lithiation of the Si nanowire, significantly deviated from the 0 to +2 V (versus Li) window used in a conventional Li–Si half-cell. This large negative potential is different from a standard Li battery, due to a potential drop needed for activated ionic transport in the Li₂O, which does not have high Li⁺ ion conductivity at room temperature.^{40,41} However, as we show below, once the lithium reaches the silicon, the diffusion and reaction do not depend on the lithium source and the battery setup (regardless of the liquid or solid cells), and the behavior is intrinsic to the crystal structure of the host silicon nanowire.

Interestingly, the volumetric expansion of the Si nanowire after lithiation in the solid cell was highly anisotropic, exhibiting a dumbbell-shaped cross section (Figure 1e, movies S1–S3 in the Supporting Information). To test whether the anisotropic volumetric expansion was related to the contact geometry between the nanowire and the solid electrolyte, we performed lithiation tests of the same batch of Si nanowires with a liquid cell in a flooding geometry (with the entire nanowire immersed in the liquid electrolyte). Similar anisotropic volumetric expansion and phase transformation to that in a solid cell was also observed in the liquid cell (Figure 1f), and both are in sharp contrast to the round shape of the pristine Si nanowires (Figure 1g), indicating that the phase transformation and deformation were intrinsic to the process of Li insertion into Si. This result also verifies that the dumbbell shape is independent of the lithium sources (from either Li or LiCoO₂), lithium transport media (Li₂O, Li_xAu or an electrolyte containing lithium salts), or lithiation conditions such as applied mechanical loading states, i.e., disregarding the stress of the nanowires pushing against the solid Li counter-electrode or merely immersed stress-free in the liquid electrolyte. Hence,

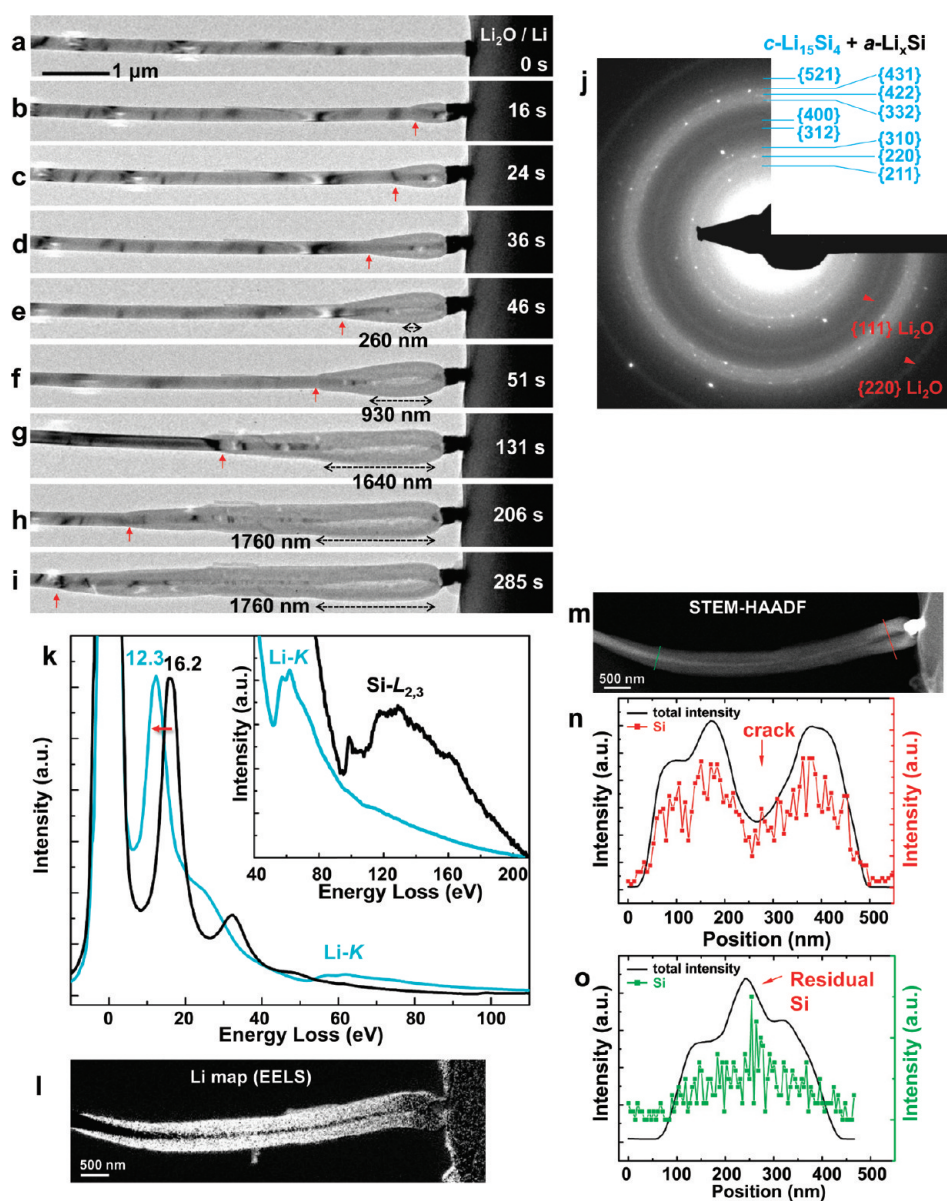


Figure 2. Crack formation of a lithiated silicon nanowire. (a–i) Morphology evolution of the Si nanowire during lithiation in the solid cell. Shortly after contacting the $\text{Li}_2\text{O}/\text{Li}$ electrode, the Au cap was lithiated and elongated (b) followed by lithiation of the Si nanowire (b–i). The red arrows mark the reaction fronts at different stages. The diameter increased from 216 nm of the pristine nanowire to 580 nm of the lithiated wire close to the Au cap. A crack developed as the residual Si core was depleted (e–i). (j) EDP showing the formation of polycrystalline $\text{Li}_{15}\text{Si}_4$ ($c\text{-Li}_{15}\text{Si}_4$), Li_2O , and an amorphous Li_xSi ($a\text{-Li}_x\text{Si}$) alloy. (k) Comparison of the electron energy loss spectra (EELS) of the pristine and lithiated Si nanowires. The primary plasmon peak shifted from 16.2 to 12.3 eV (marked by the red arrow). The inset spectra show that the Li K-edge peak emerged at ~ 55 eV and Si L-edge decreased significantly in 99–150 eV. (l) Lithium map by EELS showing the predominant lithium distribution in the $\text{Li}_{15}\text{Si}_4$ shell. The $c\text{-Si}$ core shows dark contrast, indicating little lithium present. The mapping was obtained using a spectrum imaging technique in Digital Micrograph. The energy filter for Li K-edge was from 40 to 80 eV with a step of 3 eV. The Si L-edge was outside of the energy window, thus the Si signal was negligible. (m) STEM-HAADF image of the nanowire. The crack showed dark contrast, indicating less material (lower average Z) present. The STEM image was collected with a camera length of 120 mm. (n, o) Line scans along the red and green lines in (m), respectively, showing the total intensity profile which is proportional to the sample mass thickness (dark lines), and Si K_{α} EDX intensity profile (red and green lines in (n) and (o), respectively), confirming the presence of a crack (n) and a residual $c\text{-Si}$ core (o) from the lithiated nanowire.

the results reflect an intrinsic solid-state Li–Si alloying process at ambient temperature.

Figure 2 shows the microstructure evolution and characterization of a Si nanowire upon lithiation in a solid cell. A few seconds after the Si nanowire with a gold catalyst particle on its tip touches the Li_2O (Figure 2a), lithiation initiates at the Au cap, leading to

its elongation (Figure 2b). Lithiation then propagates to the Si nanowire (Figure 2b), and a reaction front (pointed out by red arrows in panels b–i of Figure 2) propagates progressively along the axis of the nanowire. During this reaction, lithiation near the outer surface of the nanowire proceeds faster than that near the center, resulting in the formation of a lithiated shell with an

unreacted crystalline Si (*c*-Si) core. Huge deformation of the gold cap was observed in both the solid and liquid cells, but lithiation of Si nanowires does not appear to be altered by the presence of the gold particles in either case (Figure S2, Supporting Information). The unreacted *c*-Si core exhibits a tapering shape, with its diameter decreasing in the direction from the reaction front toward the point of initial contact. For the nanowire shown in Figure 2, at the point the *c*-Si core disappears, i.e., where the Si was completely amorphized by lithium insertion, a nanocrack formed (Figure 2e). The crack continues to grow as the lithiation front progresses further along the wire (Figure 2e–i and Figure S3 and Movies S4–S6 in the Supporting Information). Within about 200 s, the crack length grows from 260 to 1640 nm during the initial lithiation stage (Figure 2e–g), but then crack growth stops as the *c*-Si core is not completely consumed (Figure 2g–i). Through the application of a positive potential (+2 V) on the Si nanowire with respect to the Li counter-electrode, the lithiated Si nanowire can be delithiated and the crack length decreased (Figure S4, Supporting Information).

To characterize the lithiated nanowire, electron diffraction patterns (EDPs) were captured that indicate the coexistence of the crystalline $\text{Li}_{1.5}\text{Si}_4$ (*c*- $\text{Li}_{1.5}\text{Si}_4$) and Li_2O phases, as well as the amorphous Li_xSi (*a*- Li_xSi) alloy (Figure 2j). Identification of *c*- $\text{Li}_{1.5}\text{Si}_4$ as the fully lithiated phase,⁹ consistent with previous in situ X-ray diffraction measurements,^{4,5,20,27} was made by rigorous diffraction analyses in comparison with simulations of the seven known crystalline Li_xSi phases, including LiSi ($x = 1$), $\text{Li}_{1.2}\text{Si}_7$ ($x = 1.71$), Li_7Si_3 ($x = 2.33$), $\text{Li}_{1.3}\text{Si}_4$ ($x = 3.25$), $\text{Li}_{1.5}\text{Si}_4$ ($x = 3.75$), $\text{Li}_{2.1}\text{Si}_5$ ($x = 4.2$), and $\text{Li}_{2.2}\text{Si}_5$ ($x = 4.4$);^{16,42} see details in the Supporting Information (Figure S5). The EDP *d*-spacing and the diffraction intensity obtained from our experiments match excellently with that of the *c*- $\text{Li}_{1.5}\text{Si}_4$ phase. The formation of Li_xSi alloy is also characterized by significant changes in the electron energy loss spectra (EELS) of the Si nanowire after lithiation (Figure 2k): (1) the primary plasmon peak shifts from 16.2 eV down to 12.3 eV (indicated by the red arrow); (2) the Si L-edge significantly decreases (inset of Figure 2k, onset at ~ 99 eV); and (3) the Li K-edge emerges around 55 eV as the dominant peak in 40–240 eV range. The energy resolution of our spectrometer is 1.5 eV (dispersion: 0.3 eV/channel). The Li distribution map in the energy loss window (40–80 eV, well below the onset of Si-L_{2,3} edge at 99 eV) shows a clear picture of the lithiated shell and the unreacted *c*-Si core. The results are consistent with scanning transmission electron microscopy high angle annular dark field (STEM-HAADF) imaging (Figure 2m), showing the *Z* contrast (*Z*: atomic number) of the nanowire. In the central dark region near the nanowire tip, the core shows a reduction in high-*Z* Si ($Z = 14$), confirming the formation of a crack in the center of the lithiated section of the nanowire. Panels n and o of Figure 2 show line scans across the crack (red lines in panels m and n of Figure 2) and the partially lithiated part (green lines in Figure 2m,o) of the nanowire, respectively. The crack is revealed by an intensity dip in both the *Z*-contrast intensity (black line in Figure 2n) and the Si $\text{K}\alpha$ (1.7 keV) energy-dispersive X-ray spectroscopy (EDX) intensity (red trace in Figure 2n). In contrast, Figure 2o indicates that average *Z* is significantly lower in the $\text{Li}_{1.5}\text{Si}_4$ shell than in the residual *c*-Si core due to the low *Z* of lithium ($Z = 3$) and the much diluted atomic concentration of Si ($\sim 21\%$) in the alloy shell.

Figure 3 shows the crystallography of the anisotropic expansion in another Si nanowire during lithiation. The pristine Si nanowire had uniform diameter and a twin boundary parallel to

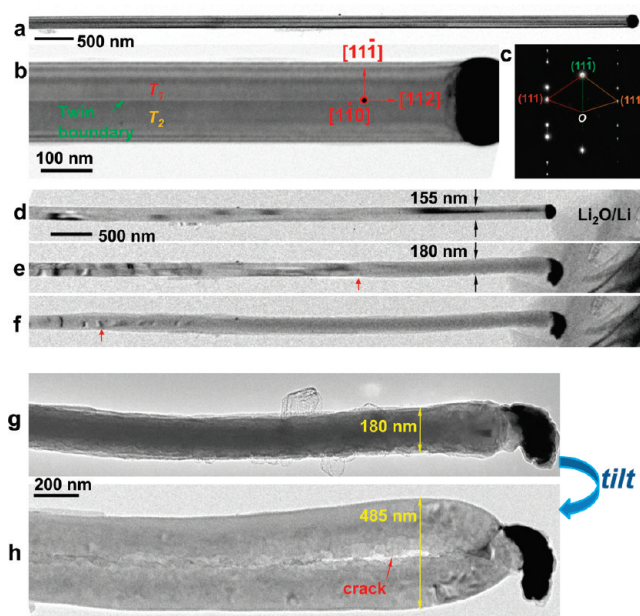


Figure 3. Anisotropic swelling and crack formation of Si nanowire during lithiation. (a) Pristine straight Si nanowire with uniform diameter. (b) High magnification image of the pristine Si nanowire with a visible twin boundary in the center. (c) EDP showing the twin viewed along the $[1\bar{1}0]$ zone axis. The axis of the nanowire was along $[112]$, and the twin boundary was parallel to $(11\bar{1})$. (d–f) Lithiation of the Si nanowire. The visible diameter expansion was only 17% and no elongation was observed. The red arrows mark the longitudinal reaction fronts. Note the contrast of the image changed from single crystalline to that of gray polycrystalline. (g, h) Lithiated nanowire in (f) viewed along $[1\bar{1}0]_{\text{Si}}$ (g) and close to $[11\bar{1}]_{\text{Si}}$ (h) directions, respectively, showing the anisotropic volumetric expansion.

the axis (Figure 3a,b). The EDP confirmed the following same orthogonal directions as that shown in Figure 1b–d: $[112]$ was the growth direction; $[11\bar{1}]$ was the norm of the twin boundary; $[1\bar{1}0]$ was the electron beam incident direction (Figure 3b,c). Viewed from the $[1\bar{1}0]$ direction, lithiation of the nanowire revealed only a 17% diameter expansion, from the original 155 to 180 nm (Figure 3d–f). However, tilting of the lithiated nanowire to a viewing direction closer to $[11\bar{1}]$ showed a much larger expansion (from the original 155 to 485 nm, Figure 3g,h) and also an obvious crack in the center of the nanowire (Figure 3h). Observations on other nanowires confirmed the same anisotropic expansion: the diameter expands by $\sim 170\%$ along $\langle 110 \rangle$ but less than 20% along $\langle 111 \rangle$ directions (Figure S6, Supporting Information). It is worth noting that the planar defect, i.e., the twin boundary parallel to the $(11\bar{1})$ plane, was not the cause of the anisotropic deformation, as the twin boundary was parallel to the long axis of the dumbbell rather than the short axis. In other words, a single twin (T_1 or T_2) itself also underwent the anisotropic deformation upon lithiation. Hence, we conclude that the twin boundary does not affect the lithiation and swelling, as might be expected since the atomic structure of coherent twin boundary requires no disruption of the covalent sp^3 bonding of silicon.

We conducted lithiation on many Si nanowires, with all showing consistent anisotropic volumetric expansion. The reaction front migration distance L was measured for both solid-cell and liquid-cell lithiation, which was found to be approximately linear with respect to the reaction time, $L \propto t$ (Figure 4). This

indicates that the kinetics of lithiation are likely controlled by short-ranged processes near the reaction front (interfacial diffusion and reaction, with adjacent plastic flow), and not by long-ranged diffusive transport along the length of the wire. This is in sharp contrast to the $L \propto t^{1/2}$ behavior found in the lithiation of SnO_2 nanowires in prior studies using a liquid-cell setup.³³ Intriguingly, crack-induced fracture of the $\text{Li}_{15}\text{Si}_4$ nanowire was also observed at some extreme situations (Figure S7, Supporting Information). Figure S7a shows a split $\text{Li}_{15}\text{Si}_4$ nanowire in the fast lithiation process polarized at -4 V against Li metal. The nanowire was fractured into two subwires (Figure S7b–d) along the central crack (Figure S7e). Due to the limitations against such

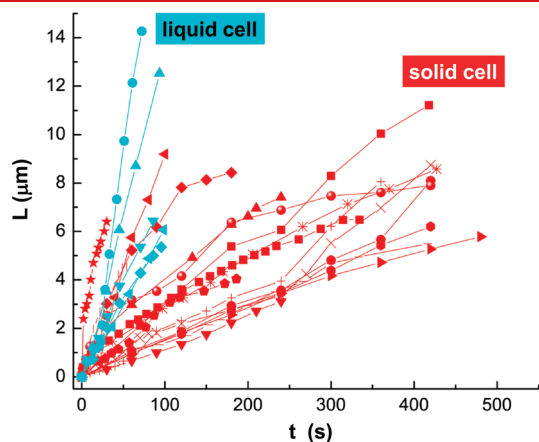


Figure 4. Statistics of the reacted Si nanowire length (L) versus time (t) plot. The linear $L-t$ relationship was observed for both the solid and the liquid cells for the same batch of Si nanowires. The reaction front migration speed was about 10–200 nm/s in the solid cell and about 60–200 nm/s in the liquid cell. The larger variation of the speed in the solid cell was likely due to the variation of Li^+ transport in the Li_2O electrolyte.

strong electric potentials in the liquid cell geometry, a similar self-splitting phenomenon has not been observed in that case, but the fracture phenomenon shows a clear link to the more common anisotropic swelling phenomenon observed in all conditions. In cases when the Li_2O electrical isolation layer is not thick enough, and we see a short circuit between the Si nanowire and the Li metal, then the lithiation proceeds rapidly at 0 V applied potential with the same fracture phenomenon. Thus, we conclude that the fracture is related to the fast lithiation of the nanowire and not the strong potential (-4 V) used in the solid cell.

To understand the anisotropic swelling and fracture in the lithiated nanowire, we modeled Li diffusion coupled to elastoplastic deformation (Figure 5a). The diffusion was described by a nonlinear model (Supporting Information) with diffusivities depending on the local Li concentration, giving an evolving core–shell structure with the sharp interface separating a Li-deficient core (ratio of Li to Si, $x \approx 0$) and Li-rich shell ($x \approx 3.75$). Figure 5b shows the simulated Li distribution in the wire, demonstrating the progressive development of the three-dimensional tapered c -Si core (Figure 5c). Numerical studies indicate that the small taper of the core is the manifestation of faster Li diffusion on the cylindrical surface than in the bulk of the wire, as suggested by the recent first principles calculations of lithium migration barriers.¹² To capture the anisotropic dimensional change of the cross section, we have matched the model to the observed cross-sectional shape by using an appropriate anisotropic lithiation-induced strain, i.e., 150% in $[1\bar{1}0]$ and 40% in $[11\bar{1}]$ at the lithiation limit of $x = 3.75$ (see Figure S8c, Supporting Information). Moreover, our model indicates that the lithiation reaction front (i.e., the core–shell interface) should move much faster in the $[1\bar{1}0]$ direction than $[11\bar{1}]$, in order to facilitate the development of dumbbell-shaped cross sections in finite element calculations (Figure S9, Supporting Information). Such anisotropy in migration velocity of the reaction front was realized numerically by assigning the anisotropic Li diffusivities.

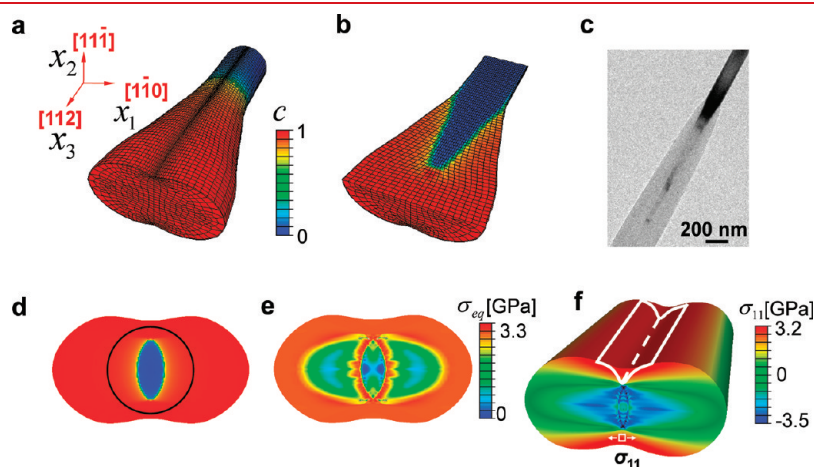


Figure 5. Simulated Li and stress distributions in a $[112]$ -oriented Si nanowire. (a) 3D simulation of a progressively lithiated nanowire (i.e., the Li flux is prescribed at the front end), showing the development of the dumbbell-shaped cross section along the longitudinal direction. The contour indicates the normalized Li concentration, c , defined as the actual Li concentration divided by the Li concentration in the fully lithiated state ($x = 3.75$). (b) The wire is cut to expose the Li distribution in the $(11\bar{1})$ cross section, showing the tapered Si core structure, which is consistent with the TEM image of (c). (d) The Li distribution, c , in the (112) cross section at a representative postnecking stage, showing the $[1\bar{1}]$ -elongated Si core. The black circle indicates the initial cross section of the pristine Si nanowire. (e) Distribution of the von Mises equivalent stress, $\sigma_{\text{eq}} = (3\sigma_{ij}\sigma_{ij}/2)^{1/2}$, corresponding to the Li distribution in (d); the areas in red attain plastic yielding. (f) Schematic of neck growth along the longitudinal direction of the nanowire. The front cross section shows the distribution of the normal stress component, σ_{11} . At the plane of $x_1 = 0$, σ_{11} is tensile near the surface indent and compressive in the center, the diminishing of central compression with increasing indent facilitates unstable necking growth (indicated by white lines) that can progress to form cracks.

That is, the apparent Li diffusivity in the (112) cross section was taken to be 100 times larger in $[1\bar{1}0]$ than in $[11\bar{1}]$. It should be emphasized that the assignment of anisotropic diffusivities in our diffusion simulation serves as an effective numerical approach to capture the crystal orientation-dependent migration velocity of the reaction front, which is actually a two-phase boundary separating the *crystalline* core and *amorphous* shell (see Supporting Information). The physical origin of large anisotropies of the lithiation strain and migration velocity of the reaction front is not well understood yet. However, it is expected to be controlled by the atomic processes of accommodating large volumetric strains at the crystal–amorphous interface that depend sensitively on the crystallographic orientation; similar interface-mediated anisotropic responses have been observed in both oxidation and wet etching of *c*-Si.^{43–45} Understanding their mechanistic basis requires a systematic study of lithiation reactions,⁴⁶ accounting for factors such as the interfacial energy and reactive layer,⁴⁷ the bond density and states near the interface,⁴³ stress effects on reaction and diffusivity,^{48,49} etc.

The progressive lithiation causes the buildup of high stresses, leading to plastic flow and fracture in the wire. In a first approximation, we adopted an elastic perfectly plastic model with a yield stress of 3 GPa.⁵⁰ Our simulations (Movies S7–S10, Supporting Information) clearly show the lithiation-induced anisotropic expansion, plastic flow of the lithiated shell, and onset of necking instability, leading to the formation of a dumbbell-shaped cross section. The table in Figure S8c lists the simulated cross-sectional geometry of a fully lithiated wire, consistent with experimental measurements. Figure 5d shows the core–shell structure with a sharp lithiation reaction front at a post-necking stage, and Figure 5e shows the corresponding contour of the von Mises stress (red indicates attainment of the plastic yield stress). In the experiments (Figure 2), the formation of surface cracks was observed at the cross section, in the region where the *c*-Si core was fully amorphized. To explain this fracture mode, we note that the present necking instability is driven by the internal expansion associated with lithiation of the Si core. Because of the absence of the external load, the resultant stress integral on any plane of the wire has to be zero, such that both the tensile and compressive stresses must coexist. Figure 5f confirms this by showing the distribution of the stress component normal to the nanowire axis, σ_{11} , at a typical postnecking deformation stage; on a central x_2 – x_3 plane ($x_1 = 0$). The stress is tensile near the surface indent and compressive in the Si core (Figure S10c,d, Supporting Information). The former tends to drive the growth of the neck and facilitate the initiation of a surface crack, while the latter resists this crack initiation. As lithiation proceeds, the *c*-Si core is reduced, leading to diminishment of the region of compressive stress. The vanishing compressive stresses near the center of the wire allow the unstable growth of the indent that progresses to form cracks and may eventually lead to a splitting of the wire (Figure S7, Supporting Information).

Our detailed observations and modeling have several important implications for the development of Si anode materials for LIBs. First, lithiation of crystalline Si leads to highly anisotropic transformation strains of the $\text{Li}_{15}\text{Si}_4$ product which promote fracture, but this process could be mitigated. For example, orienting the nanowires along a $\langle 110 \rangle$ crystallographic axis could promote wire lengthening as the primary volumetric expansion mechanism. Second, if conductive coatings are applied to the surface of the nanowires, these coatings are more likely to remain intact along $\langle 111 \rangle$ -containing surfaces of the nanowire, as the

expansion is lower in the $\langle 111 \rangle$ directions. Third, the use of amorphous Si as an anode material would likely remove the anisotropy associated with initial lithiation and could suppress fracture.

CONCLUSIONS

Taking advantage of the electron transparency of nanowires, we performed real-time in situ TEM observations of the lithiation of Si nanowires to identify the morphology changes associated with lithiation. We have directly observed that the large volumetric expansion as Si converts to $\text{Li}_{15}\text{Si}_4$ occurs in a highly anisotropic fashion in free-standing nanowires of $\langle 112 \rangle$ growth directions, resulting in intermediate dumbbell-shaped cross sections. Despite extensive plastic flow of the lithiation product, very large tensile stresses nevertheless develop inside the nanowire during Li insertion, causing a necking instability and fracture.

ASSOCIATED CONTENT

S Supporting Information. Experimental details for Si nanowire preparation, in situ electrochemical devices construction, electron microscopy, and modeling. This material is available free of charge via the Internet at <http://pubs.acs.org>.

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